

**1. Scope :**

This specification applies to silicon zener double diodes chips,  
Device NO. SD-511A6G

**2. Application :**

The thermal path shall be electrically neutral within the package, Zener diode chip must be mounted on the thermal path and isolated the metal electrodes electrically.

**3. Structure :**

- 2-1. Planar type : P/N/P, Zener Double Diodes.
- 2-2. Electrodes :  
 Top side : Gold pad .  
 Back side : Isolation layer.

**4. Size :**

- 3-1. \*Chip size : 11.0 mils x 11.0 mils (0.280 mm x 0.280 mm ).
- 3-2. Chip thickness :  $6.0 \pm 1.0$  mils ( $0.150 \pm 0.025$  mm ).
- 3-3. Active area : 7.3 mils x 7.3 mils x 1/2 x 2 (0.186 mm x 0.186 mm x 1/2 x 2).
- 3-4. Dual Bonding pad : 6.8 mils x 6.8 mils x 1/2 x 2 (0.173 mm x 0.173 mm x 1/2 x 2) .  
 Height of hypotenuse : 5.23 mils (0.133 mm)
- 3-5. Pattern drawing : Refer to the attached drawing.

\*Including scribing line. The chip size is about  $(0.250 \pm 0.015)^2 \text{mm}^2$  after dicing.

**5. Electrical characteristics (Ta = 25 °C)**

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse Leakage Current	$I_R$	$V_R=20V$ $E_e=0\text{mW/cm}^2$			0.5	$\mu A$
Zener Voltage	$V_Z$	$I_Z=5\text{mA}$ $E_e=0\text{mW/cm}^2$	23		29	V

